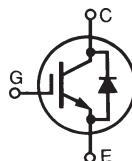


1200V XPT™ IGBT GenX3™ w/ Diode

IXYR50N120C3D1

(Electrically Isolated Tab)

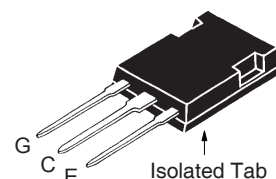
High-Speed IGBT
for 20-50 kHz Switching



$$\begin{aligned} V_{CES} &= 1200V \\ I_{C90} &= 32A \\ V_{CE(sat)} &\leq 3.5V \\ t_{fi(typ)} &= 43ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	56	A
I_{C90}	$T_C = 90^\circ C$	32	A
I_{F110}	$T_C = 110^\circ C$	18	A
I_{CM}	$T_C = 25^\circ C$, 1ms	210	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 5\Omega$ Clamped Inductive Load	$I_{CM} = 100$ @ $V_{CE} \leq V_{CES}$	A
P_C	$T_C = 25^\circ C$	290	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
V_{ISOL}	50/60 Hz, 1 Minute	2500	V~
F_C	Mounting Force	20..120/4.5..27	N/lb.
Weight		5	g

ISOPLUS247™



G = Gate C = Collector
E = Emitter

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V~ Electrical Isolation
- Optimized for Low Switching Losses
- Square RBSOA
- Positive Thermal Coefficient of $V_{ce(sat)}$
- Anti-Parallel Ultra Fast Diode
- High Current Handling Capability
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			50 μA 500 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 50A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$		4.2	3.5 V V

Symbol Test Conditions

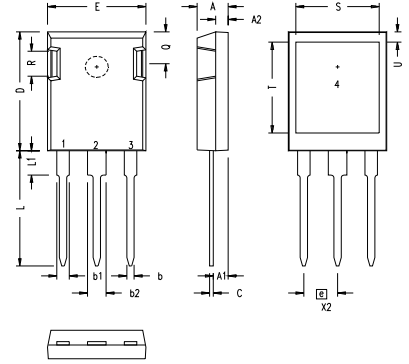
($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{fs}	$I_C = 50\text{A}, V_{CE} = 10\text{V}$, Note 1	20	32	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3100	pF
C_{oes}			230	pF
C_{res}			66	pF
$Q_{g(on)}$	$I_C = 50\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		142	nC
Q_{ge}			23	nC
Q_{gc}			60	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 50\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 5\Omega$ Note 2		28	ns
t_{ri}			62	ns
E_{on}			3.0	mJ
$t_{d(off)}$			133	ns
t_{fi}			43	ns
E_{off}			1.0	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 50\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 5\Omega$ Note 2		28	ns
t_{ri}			68	ns
E_{on}			6.0	mJ
$t_{d(off)}$			160	ns
t_{fi}			60	ns
E_{off}			1.4	mJ
R_{thJC}			0.43	$^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

ISOPLUS247 (IXYR) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - Gate
2,4 - Collector
3 - Emiiter

Reverse Diode (FRED)

($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)

Symbol Test Conditions

Characteristic Value

Min. Typ. Max.

V_F	$I_F = 30\text{A}, V_{GE} = 0\text{V}$, Note 1	$T_J = 150^\circ\text{C}$	1.75	3.00	V
I_{RM}	$I_F = 30\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}, V_R = 600\text{V}$	$T_J = 100^\circ\text{C}$		9	A
t_{rr}		$T_J = 100^\circ\text{C}$	195		ns
R_{thJC}				1.10	$^\circ\text{C/W}$

Notes:

- Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
- Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

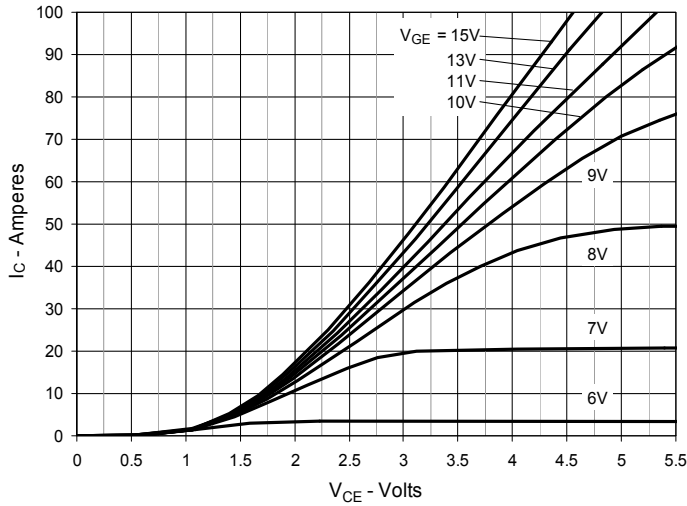


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

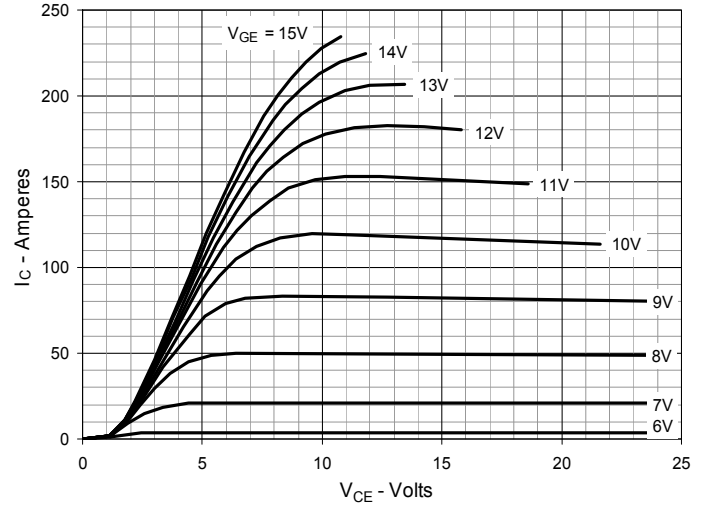


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

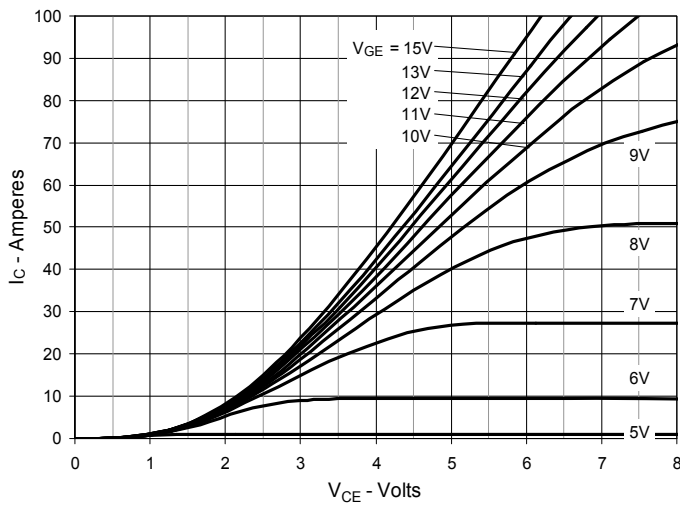


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

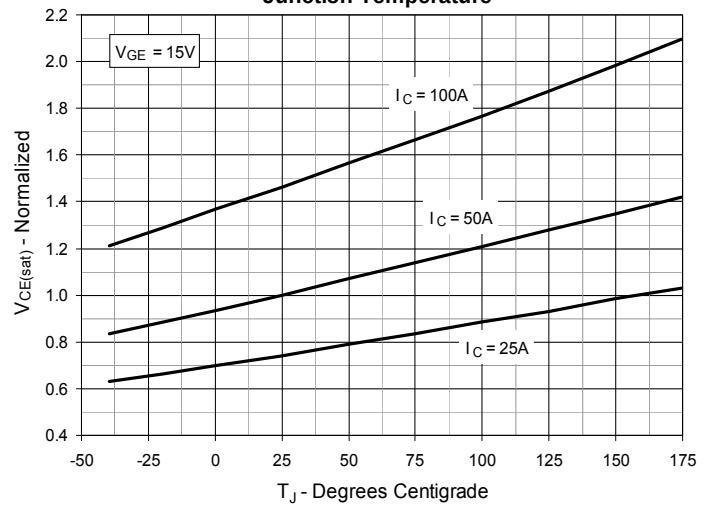


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

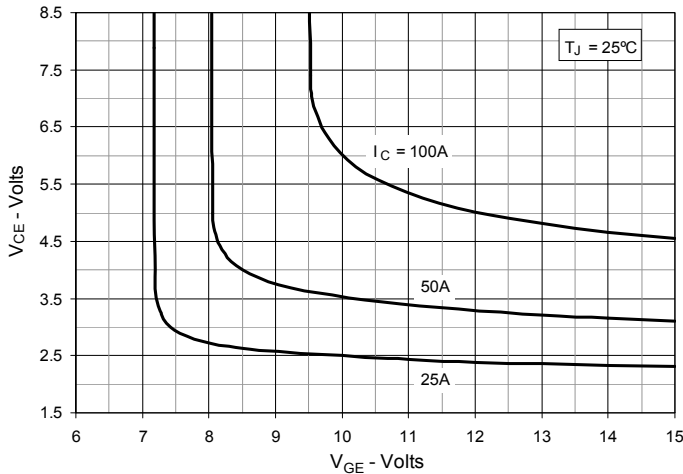


Fig. 6. Input Admittance

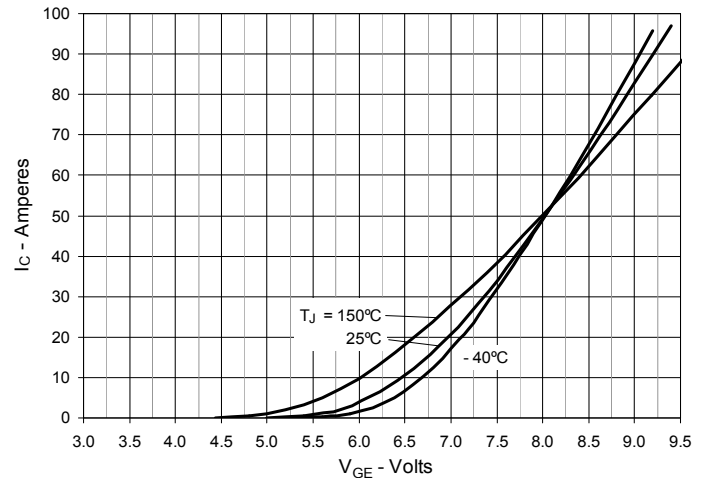


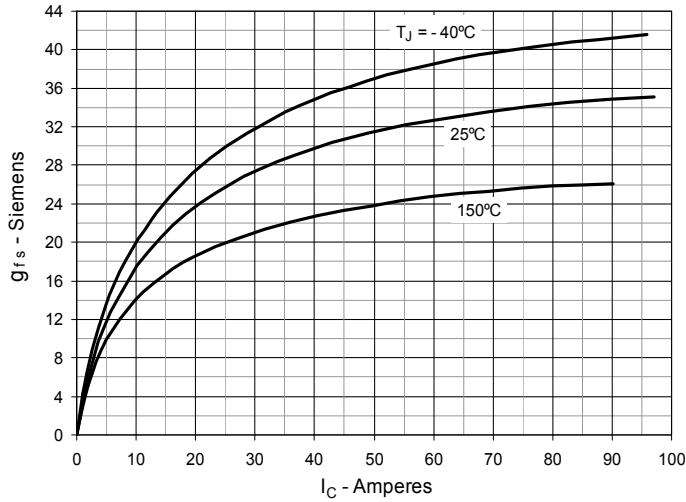
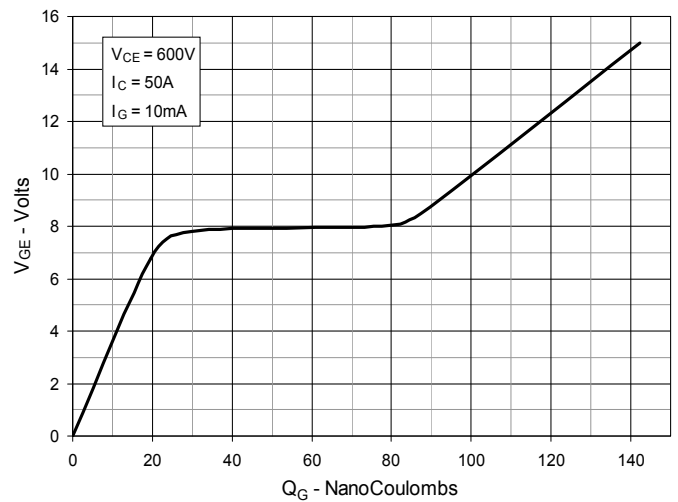
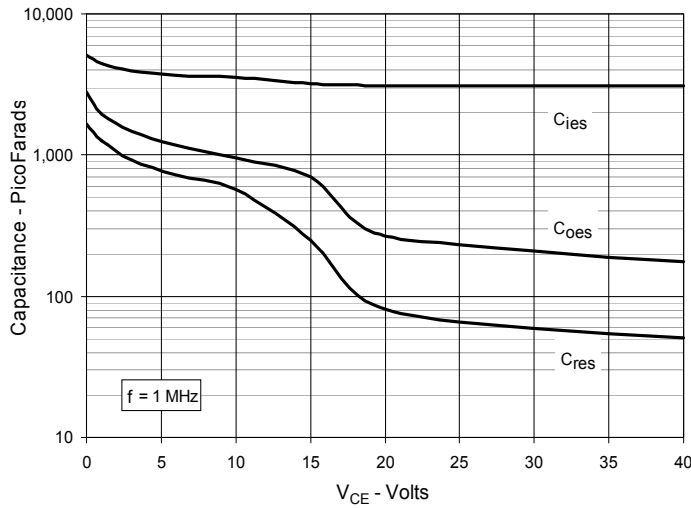
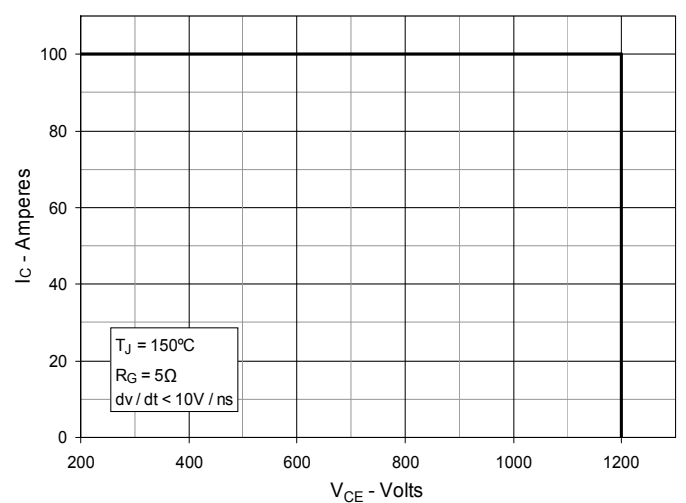
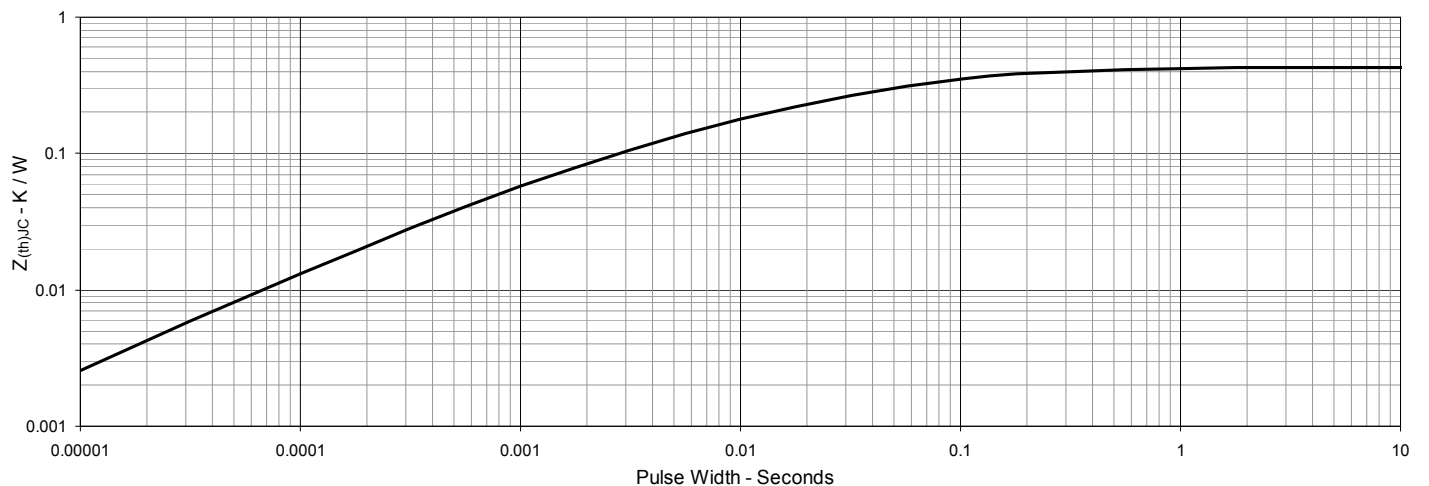
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Maximum Transient Thermal Impedance


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

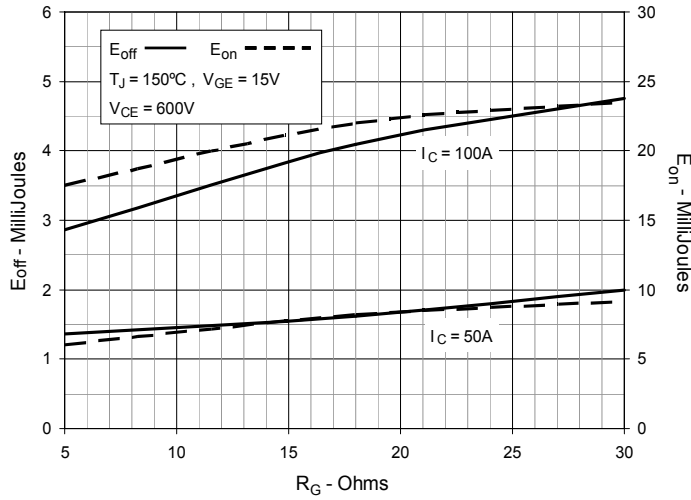


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

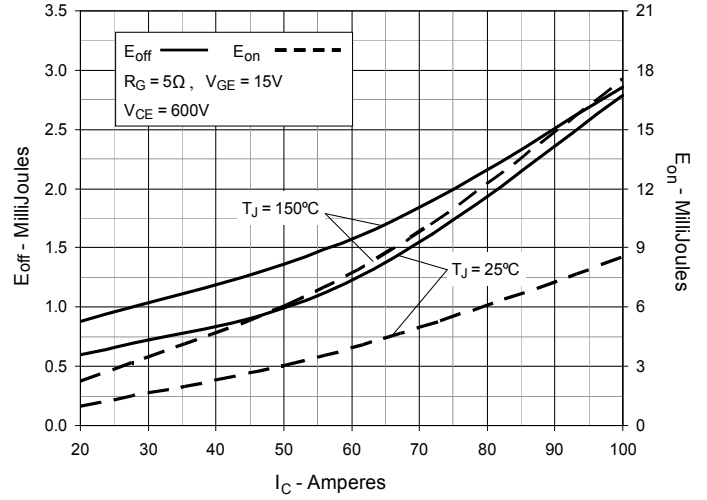


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

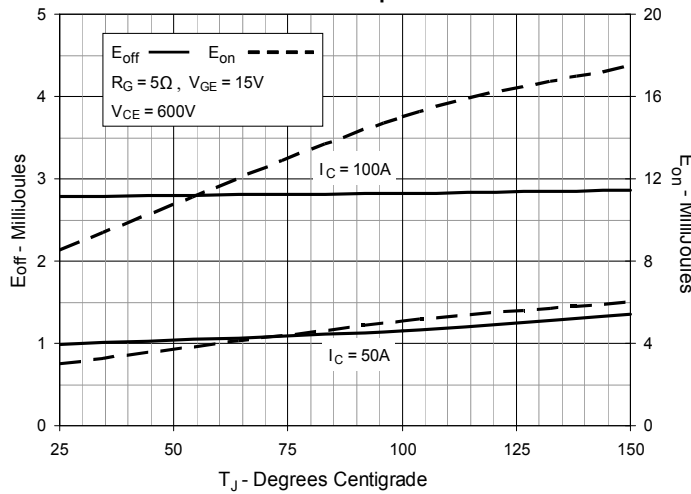


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

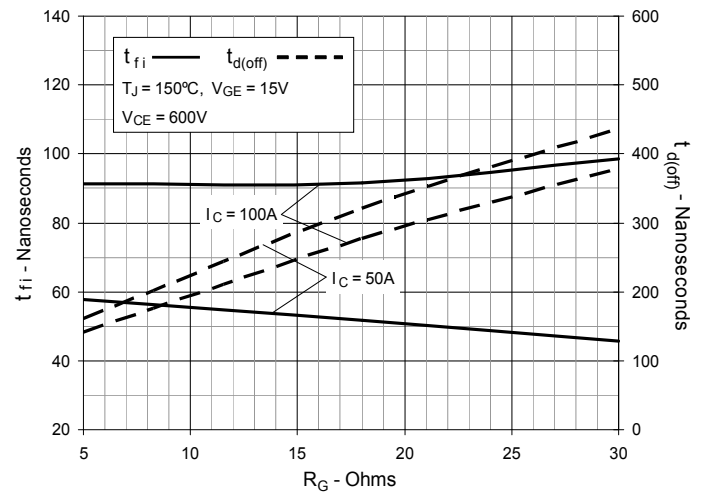


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

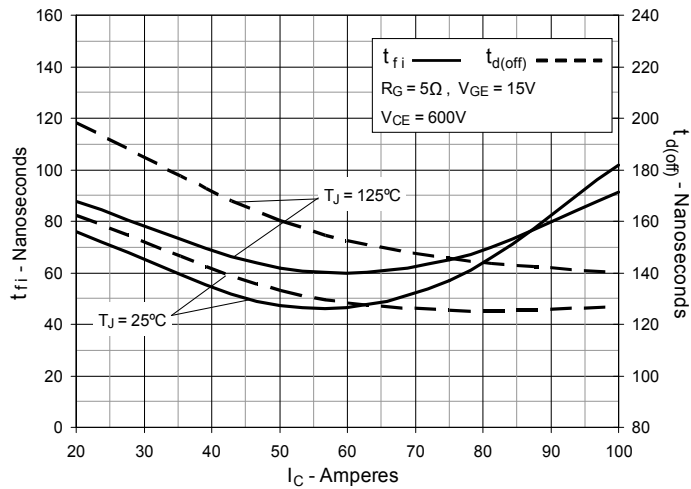


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

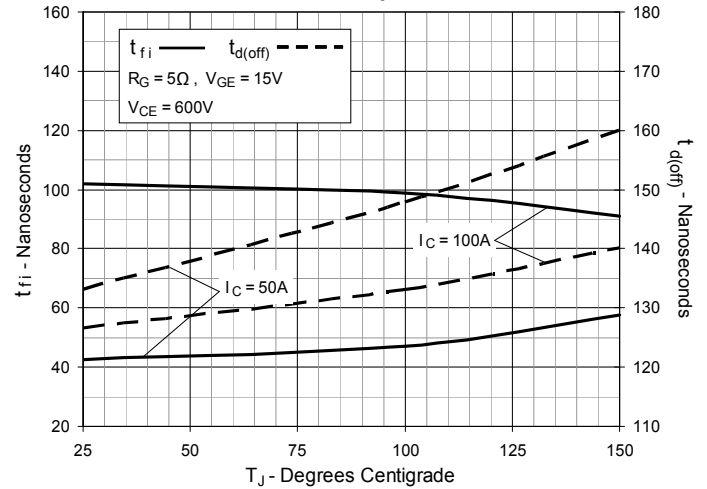


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

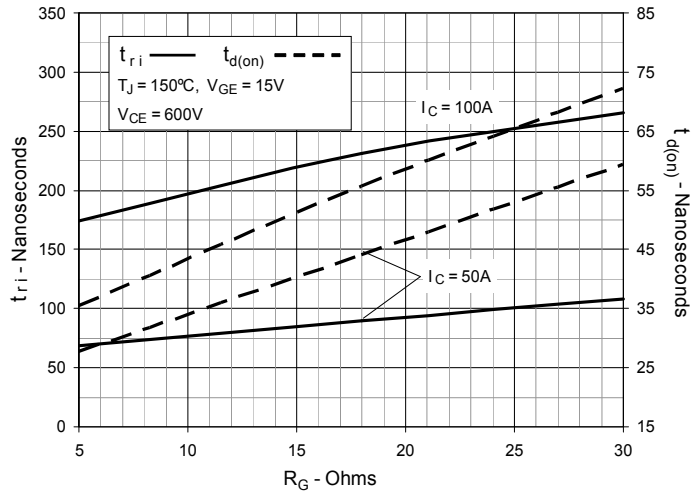


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

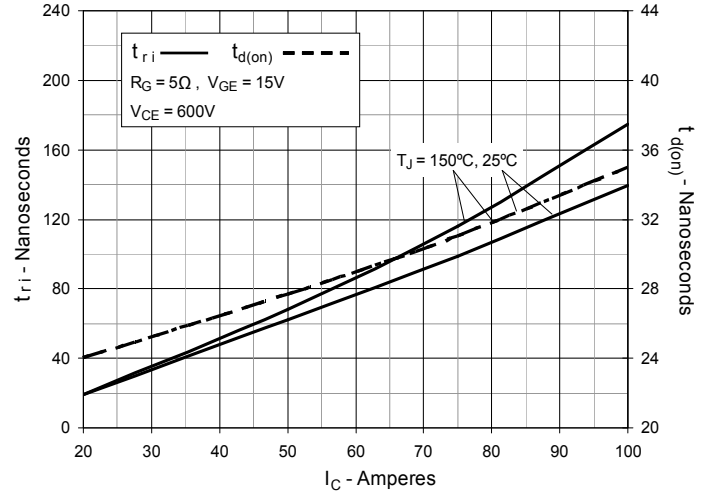


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

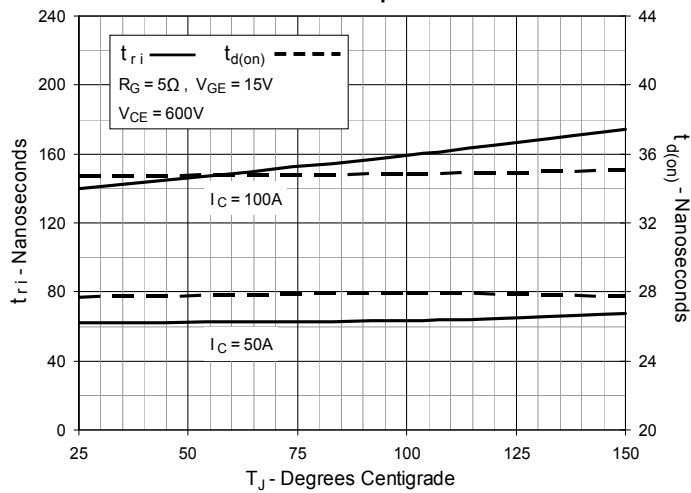


Fig. 21. Maximum Transient Thermal Impedance (Diode)

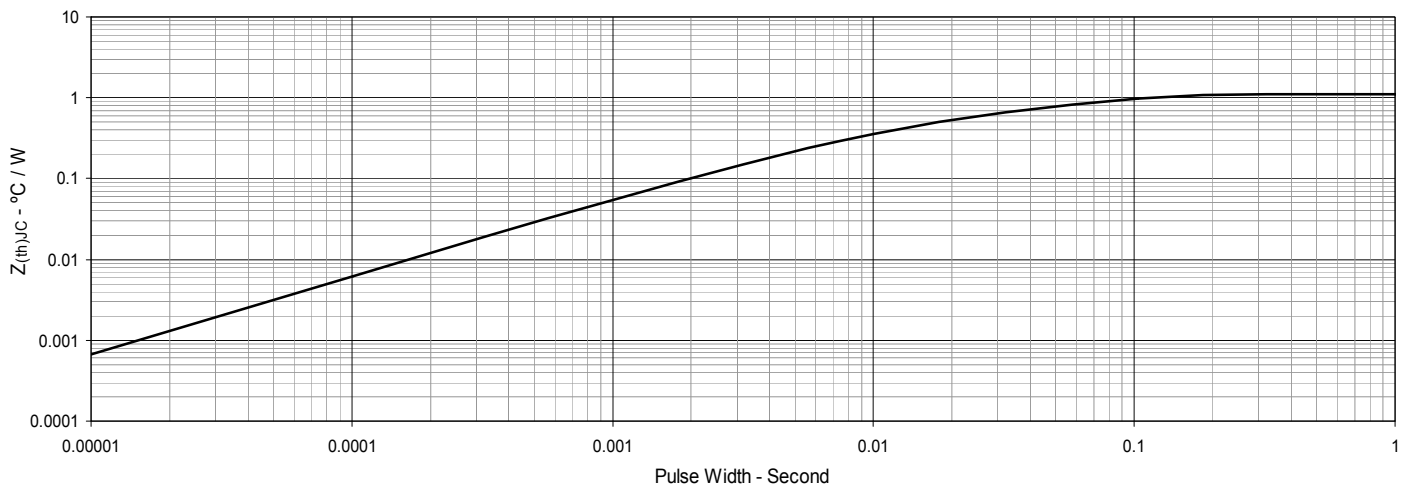


Fig. 22. Forward Current I_F vs V_F

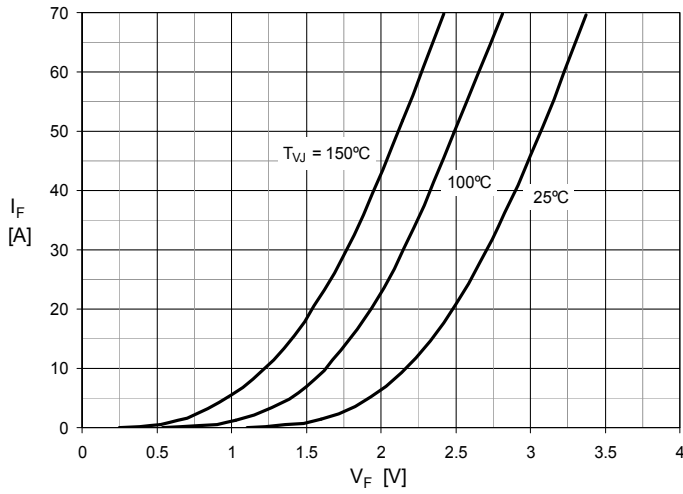


Fig. 23. Reverse Recovery Charge Q_{RM} vs. $-di_F/dt$

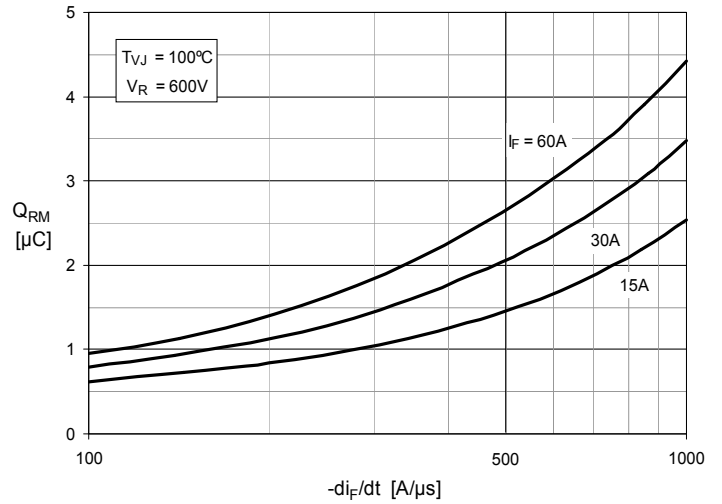


Fig. 24. Peak Reverse Current I_{RM} vs. $-di_F/dt$

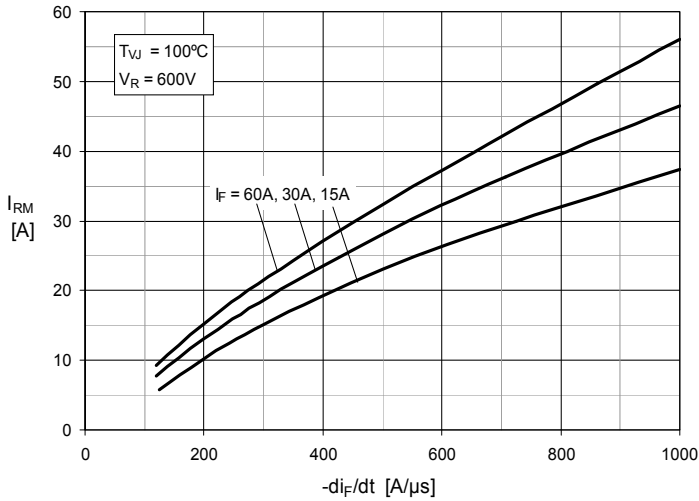


Fig. 25. Dynamic Parameters Q_{RM} , I_{RM} vs. T_{VJ}

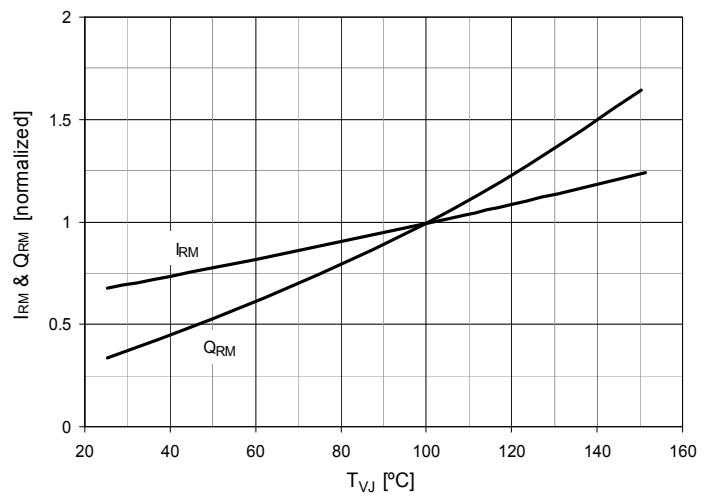


Fig. 26. Recovery Time t_{rr} vs. $-di_F/dt$

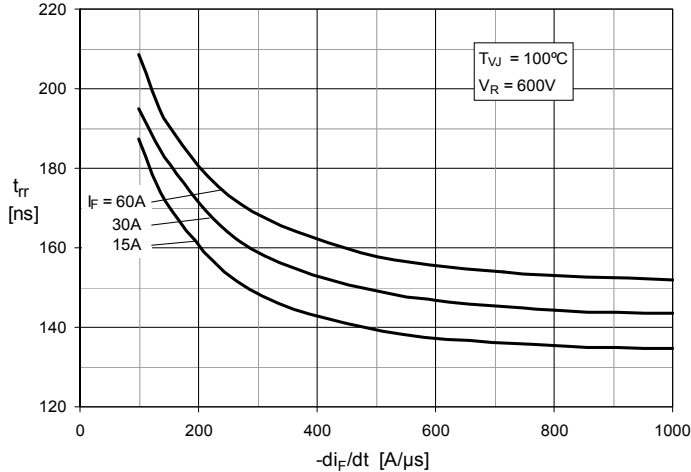
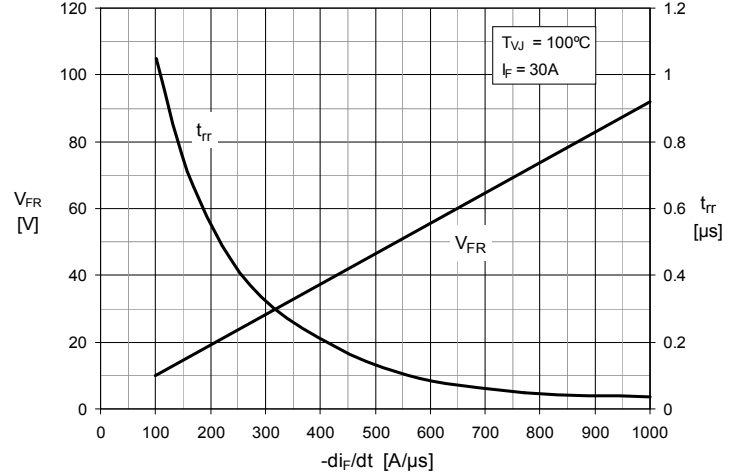


Fig. 27. Peak Forward Voltage V_{FR} , t_{rr} vs $-di_F/dt$





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